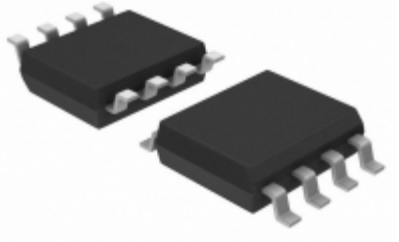


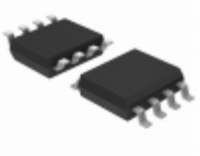
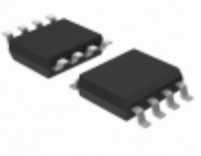
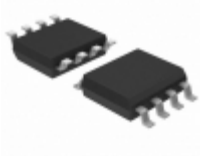
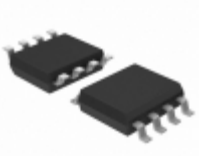

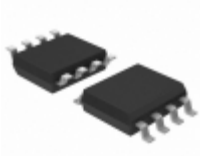
	<h2 style="color: #D9534F;">SI4102DY-T1-E3</h2>	
	Hersteller-Teilenummer:	SI4102DY-T1-E3
	Hersteller / Marke:	Electro-Films (EFI) / Vishay
	Teil der Beschreibung:	MOSFET N-CH 100V 3.8A 8-SOIC
	Datenblätter:	 SI4102DY-T1-E3.pdf
	RoHs Status:	Bleifrei / RoHS-konform
Lagerzustand:	New original, 10276 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	SI4102DY-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 100V 3.8A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	10276 pcs Stock
detaillierte Beschreibung	N-Channel 100V 3.8A (Tc) 2.4W (Ta), 4.8W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2.4W (Ta), 4.8W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.8A (Tc)
Rds On (Max) @ Id, Vgs	158 mOhm @ 2.7A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	11nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	370pF @ 50V
Antriebsspannung (Max Rds On, Min Rds On)	6V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI4102DY-T1-E3 ist neu im Original, Suche SI4102DY-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4102DY-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI4102DY-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4102DY VISHAY SI4102DY VISHAY</p>	 <p>SI4100DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 6.8A 8-SOIC</p>	 <p>SI4101DY-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 25.7A 8SOIC</p>	 <p>SI4102DY-T1-E3 Vishay / Siliconix MOSFET N-CH 100V 3.8A 8-SOIC</p>
 <p>SI4104DY-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 4.6A 8-SOIC</p>	 <p>SI4103DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CHAN 30V SO-8</p>	 <p>SI4101DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 25.7A 8SOIC</p>	 <p>SI4104DY-T1-E3 Vishay / Siliconix MOSFET N-CH 100V 4.6A 8-SOIC</p>

heiße Teile

Mehr

⊛ SI4010-C2-GT	↔ SI4010DY	⇒ SI4010DY-T1-GE3	D SI4010DY-T1-GE3	⇒ SI4012-C1001GTR
⊣ SI4021-A1-FTR	⊛ SI4022-A0-FTR	D SI4022-A1-FTR	⇒ SI4030-A0-FM	⇒ SI4032-V2-FMR
⊛ SI4033-B2-FM	⊣ SI4048DY-T1-E3	⊛ SI4056DY	↔ SI4056DY-T1-E3	⇒ SI4056SPG
D SI4058DY	⊛ SI4090DY	⊣ SI4100BDDY-T1-GE3	⊛ SI4100DY	⇒ SI4100DY-T1-E3
⇒ SI4100DY-T1-E3	↔ SI4100DY-T1-GE3	⊛ SI4100DY-T1-GE3	⊣ SI4102DY	⇒ SI4102DY-T1-E3
↔ SI4102DY-T1-GE3	⇒ SI4102DY-T1-GE3	D SI4104DY-T1-GE3	⊛ SI4104DY-T1-GE3	⊣ SI4108DY-T1-GE3
⊛ SI4108DY-T1-GE3	D SI4110DY-T1-GE3	⇒ SI4110DY-T1-GE3	↔ SI4112-D-GM	⇒ SI4113-BMR
⊣ SI4114DY	⊛ SI4114DY-T1-E3	↔ SI4114DY-T1-E3	⇒ SI4114DY-T1-GE3	⇒ SI4114DY-T1-GE3
⊛ SI4116DY	⊣ SI4116DY-T1-E3	⊛ SI4116DY-T1-E3	D SI4116DY-T1-GE3	⇒ SI4116DY-T1-GE3
↔ SI4122-BTR	⊛ SI4122-D-GMR	⊣ SI4122DY-T1-E3	⊛ SI4122G-BMR	⇒ SI4123-BM

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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